

Dephasing in Strongly Anisotropic Black Phosphorus

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Catania, 14/12/2016



Cell parameters a=3.13Å b=10.47Å c=4.37Å

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A. Morita, Appl. Phys. A 39 (1986) 227

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The reinassance of black phosphorus

(cm2/volt-sec

Р, щ

Mobility

 $E_G = 1.0eV$

0.2

Monolayer

p-type Black P

△ I // x-axis, B // z-axis ○ I // y-axis, B // z-axis □ I // z-axis, B // y-axis

emperature (K

15 20 Laver Number

Tunable Transport Gap

in Phosphorene

 $E_{\rm C} = 0.3 eV$

- In 1914 first successful synthesis (Bridgman) and in 2007 synthesis at room pressure (Lange, Nilges)
- ✓ p-type semiconductor: 0.3eV direct band gap and high hole mobility (64,000 cm²/Vs @ 20 K)
- ✓1983 (Narita): n-type doping by Te
- 2014: First publications on bP layered thin films
- Highly reactive in air
- Band-gap tunable with layer number
- In-plane anisotropy of optical and transport properties
- ✓... and much more! SdH, QH...





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Temperature (K)

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bP Field Effect Transistor





PMMA MMA Ti/Au contacts bP flake HMDS SiO₂ thermal oxide Si





R_{xx}: 1-2 R_{xy}: 1-3

Flake thickness: 65 ± 2 nm

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Transport Characterization



 $p \sim V_g$ for $V_g < -30$ V

$$p = 10^{13} \text{ cm}^{-2} \text{ for } V_g = -30 \text{ V}$$

- Field-effect mobility μ: 300 cm²/Vs at V_g = -70 V
- Negligible T-dependence in μ for 0.26 K < T < 20 K



Longitudinal magnetotransport measurements



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Weak Localization

Weak localization is a quantum effect related to coherent scattering at low temperatures.



Picture from Bergmann, Weak localization in thin films, Physics Reports 107, 1984







Hikami-Larkin-Nagaoka model

$$\Delta \sigma = -\frac{e^2}{2 \pi^2 \hbar} \left(\Psi \left(\frac{1}{2} + \frac{B_1}{B} \right) - \frac{3}{2} \Psi \left(\frac{1}{2} + \frac{B_2}{B} \right) + \frac{1}{2} \Psi \left(\frac{1}{2} + \frac{B_3}{B} \right) \right)$$

Where Ψ is the digamma function

$$B_1 = B_0 + B_{so} + B_s$$
$$B_2 = \frac{4}{3}B_{so} + \frac{2}{3}B_s + B_{\phi}$$
$$B_3 = 2B_s + B_{\phi}$$

S. Hikami, A. I. Larkin, and Y. Nagaoka, Prog. Of Theor. Phys. 63 (1980) 707.

1/1/10/0016

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Weak Localization



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Scattering Lengths

- Dephasing length vs. inelastic scattering time: $L_{\varphi} = \sqrt{D\tau_{\varphi}}$ with D diffusion coefficient
- •Ballistic transport: $\tau_{\varphi} \propto T^{-2}$ or $L_{\varphi} \propto T^{-1}$
- Diffusive transport ($L_0 < L_{\varphi}$):

$$au_{arphi} \propto T^{-1} \; {
m or} \; L_{arphi} \propto T^{-1/_2}$$

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Lin and Bird, Jour. Phys. Cond. Mat. 14, R501, (2002)

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VOLUME 86, NUMBER 9

PHYSICAL REVIEW LETTERS

26 February 2001

Geometry-Dependent Dephasing in Small Metallic Wires

D. Natelson, R. L. Willett, K. W. West, and L. N. Pfeiffer

Bell Laboratories, Lucent Technologies, Murray Hill, New Jersey 07974 (Received 19 June 2000)

Temperature dependent weak localization is measured in metallic nanowires in a previously unexplored size regime down to width w = 5 nm. The dephasing time, τ_{ϕ} , shows a low temperature T dependence close to quasi-1D theoretical expectations ($\tau_{\phi} \sim T^{-2/3}$) in the narrowest wires, but exhibits a relative saturation as $T \rightarrow 0$ for wide samples on the same material as observed previously. As only

sample geometry is varied to exhibit constraint on models of dephasing

PHYSICAL REVIEW B, VOLUME 64, 121404(R)

Phase-coherent transport in ropes of single-wall carbon nanotubes

J. Appenzeller, R. Martel, and Ph. Avouris IBM T. J. Watson Research Center, Yorktown Heights, New York 10598

H. Stahl, U. Th. Hunger, and B. Lengeler II. Physikalisches Institut, RWTH Aachen, Templergraben 55, 52056 Aachen, Germany (Received 21 May 2001; revised manuscript received 23 July 2001; published 6 September 2001)

To study the phase breaking scattering events in single-wall carbon nanotubes (SWNTs), ropes of SWNTs are intentionally damaged by Ar⁺ ion milling. Due to this treatment, the average distance an electron can travel before being elastically scattered is reduced to about 10 nm. This significantly increases the probability of one-dimensional localization and allows us to obtain the phase coherence angth (L_{Φ}) in ropes of SWNTs as a function of temperature. We find that Nyquist scattering $(\tau_{\Phi} \sim T^{-2/3})$ as well as another dephasing mechanism with a $\tau_{\Phi} \sim T^{-1}$ dependence are involved in limit of the phase-coherence transport. We also investigate the scattering of hot electrons in the system. The results support the statement that two different scattering mechanisms dominate the phase coherence length for different rope samples.

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1 T (K) 10



Conclusions

✓ Weak localization oberved in a bP FET
 ✓ Excellent agreement with HLN model
 ✓ Dephasing length L_φ reaches 55 nm
 ✓ T-dependence of L_φ close to quasi-1D
 ✓ This seems a further proof of strong in plane anisotropy of bP

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"**Phos**phorene **fun**ctionalization: a new platform for advanced multifunctional materials"





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